

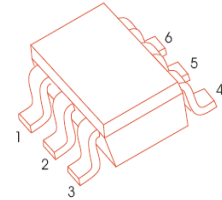
## SOT-363 Plastic-Encapsulate Diodes

**BAT54ADW /BAT54BRW /**

**BAT54CDW /BAT54SDW /BAT54TW**

SCHOTTKY BARRIER DIODE ARRAYS

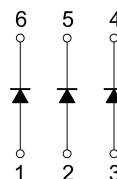
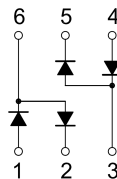
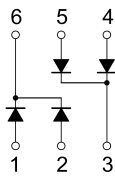
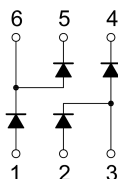
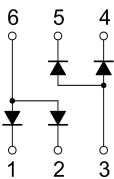
SOT-363



**FEATURES**

- Low Forward Voltage Drop
- Fast Switching
- Small Surface Mount Package
- PN Junction Guard Ring for Transient and ESD Protection
- Available in Lead Free Version

**MARKING:**



**BAT54ADW**

**BAT54BRW**

**BAT54CDW**

**BAT54SDW**

**BAT54TW**

MARKING: KL6

MARKING: KLB

MARKING: KL7

MARKING: KL8

MARKING: KLA

**MAXIMUM RATINGS (  $T_a=25^{\circ}\text{C}$  unless otherwise noted )**

Symbol	Parameter	Value	Unit
$V_{RRM}$	Repetitive Peak Reverse Voltage	30	V
$V_{RWM}$	Peak Working Reverse Voltage		
$V_R$	DC Blocking Voltage		
$I_O$	Forward Continuous Current	200	mA
$I_{FRM}$	Repetitive Peak Forward Current	300	mA
$I_{FSM}$	Non-repetitive Peak Forward Surge Current @ $t \leq 1\text{s}$	600	
$P_D$	Power Dissipation	200	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	500	$^{\circ}\text{C/W}$
$T_j$	Junction Temperature	125	$^{\circ}\text{C}$
$T_{stg}$	Storage Temperature	-55~+150	$^{\circ}\text{C}$



**ELECTRICAL CHARACTERISTICS(T<sub>a</sub>=25°C unless otherwise specified)**

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Reverse voltage	V <sub>(BR)</sub>	I <sub>R</sub> =100μA	30			V
Reverse current	I <sub>R</sub>	V <sub>R</sub> =25V			2	μA
Forward voltage	V <sub>F</sub>	I <sub>F</sub> =1mA			320	mV
		I <sub>F</sub> =10mA			400	
		I <sub>F</sub> =30mA			500	
		I <sub>F</sub> =100mA			1000	
Total capacitance	C <sub>tot</sub>	V <sub>R</sub> =1V,f=1MHz			10	pF
Reverse recovery time	t <sub>rr</sub>	I <sub>F</sub> = I <sub>R</sub> =10mA, I <sub>rr</sub> =0.1×I <sub>R</sub> , R <sub>L</sub> =100Ω			5	ns